

ABSTRACT OF THE DISCLOSURE

A method of fabricating a TFT includes a step of forming an impurity region for a source and a drain by simultaneously implanting and activating impurity ions. More particularly, the present invention includes the steps of forming a gate insulating layer and a gate on a predetermined and selected portion of an active layer, forming an excited region in the exposed portion of the active layer by implanting hydrogen ions to the active layer by using the gate as a mask, and forming an impurity region by implanting impurity ions heavily to the excited region which remains in an excited state.